

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V _{DSS}	30	V
Gate-Source Voltage			V _{GSS}	±20	V
Continuous Drain Current (Note 6) V _{GS} = 10V	Steady State	T _A = +25°C T _A = +70°C	I _D	12.4 10	A
	Steady State	T _C = +25°C T _C = +70°C	I _D	37.8 30.3	A
	t < 10s	T _A = +25°C T _A = +70°C	I _D	17 13.6	A
Maximum Body Diode Continuous Current			I _S	2	A
Pulsed Drain Current (10μs pulse, duty cycle = 1%)			I _{DM}	90	A
Avalanche Current (Note 7) L = 0.1mH			I _{AS}	22	A
Avalanche Energy (Note 7) L = 0.1mH			E _{AS}	24	mJ

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 5)	T _A = +25°C	P _D	1.6	W
	T _A = +70°C		1.0	
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R _{θJA}	75	°C/W
	t < 10s		34	
Total Power Dissipation (Note 6)	T _A = +25°C	P _D	2.8	W
	T _A = +70°C		1.8	
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R _{θJA}	46	°C/W
	t < 10s		24	
Thermal Resistance, Junction to Case (Note 6)		R _{θJC}	3.1	
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV _{DSS}	30	—	—	V	V _{GS} = 0V, I _D = 250μA
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	—	—	1	μA	V _{DS} = 30V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	V _{GS(th)}	1.3	—	2.3	V	V _{DS} = V _{GS} , I _D = 250μA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	8	12	mΩ	V _{GS} = 10V, I _D = 11A
			12	16		V _{GS} = 4.5V, I _D = 9A
Diode Forward Voltage	V _{SD}	—	0.70	1.0	V	V _{GS} = 0V, I _S = 1A
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C _{iss}	—	1415	—	pF	V _{DS} = 15V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	C _{oss}	—	119	—	pF	
Reverse Transfer Capacitance	C _{rss}	—	82	—	pF	
Gate Resistance	R _G	—	2.2	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1.0MHz
Total Gate Charge (V _{GS} = -10V)	Q _g	—	25.1	—	nC	V _{DS} = 15V, I _D = 12A
Total Gate Charge (V _{GS} = -4.5V)	Q _g	—	11.3	—	nC	
Gate-Source Charge	Q _{gs}	—	3.5	—	nC	
Gate-Drain Charge	Q _{gd}	—	3.6	—	nC	
Turn-On Delay Time	t _{D(on)}	—	4.8	—	ns	V _{DD} = 15V, V _{GS} = 10V, R _L = 1.25Ω, R _G = 3Ω,
Turn-On Rise Time	t _r	—	16.5	—	ns	
Turn-Off Delay Time	t _{D(off)}	—	26.1	—	ns	
Turn-Off Fall Time	t _f	—	5.6	—	ns	
Body Diode Reverse Recovery Time	t _{rr}	—	12.3	—	ns	I _F = 12A, di/dt = 500A/μs
Body Diode Reverse Recovery Charge	Q _{rr}	—	10.4	—	nC	

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 - Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
 - UIS in production with L = 0.1mH, starting T_A = +25°C.
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to product testing.

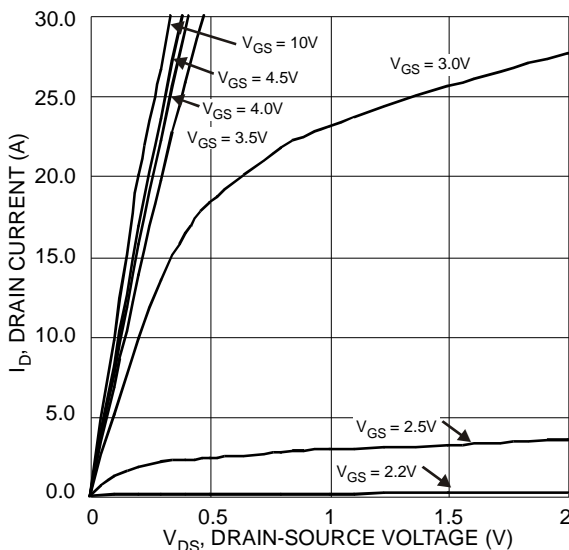


Figure 1 Typical Output Characteristic

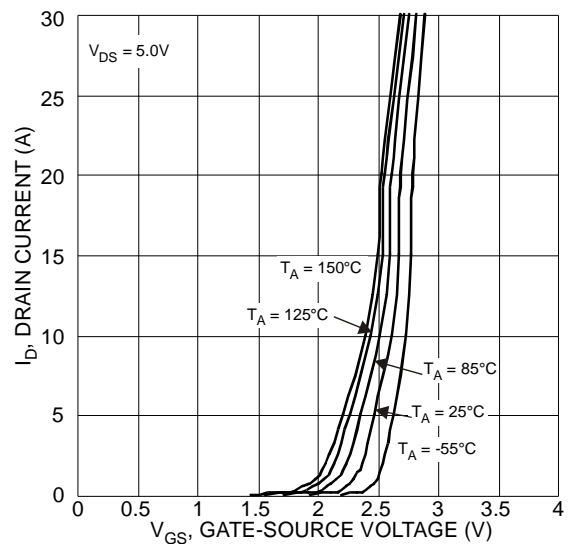
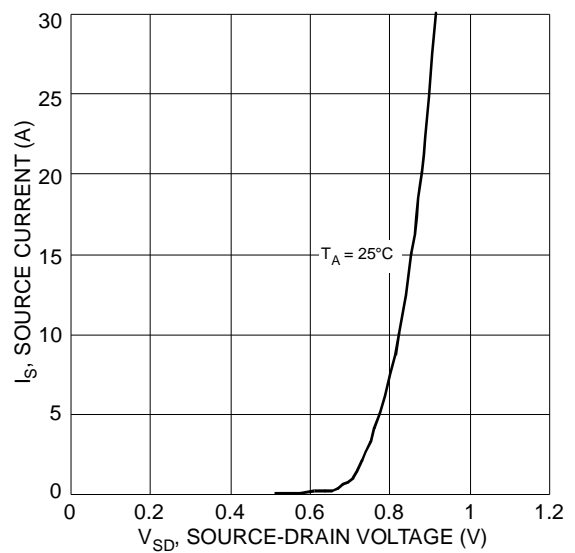
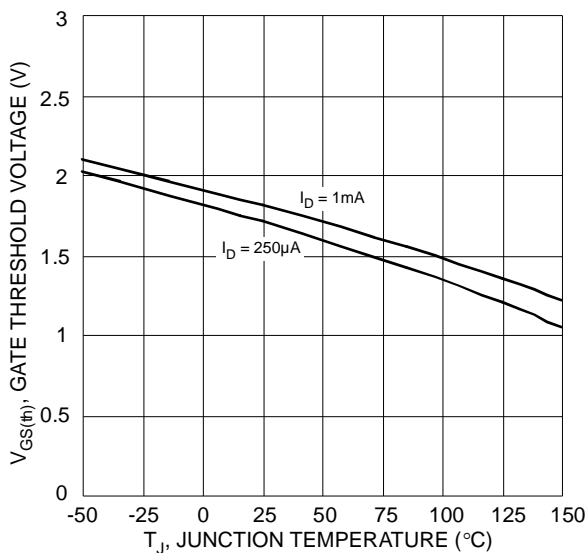
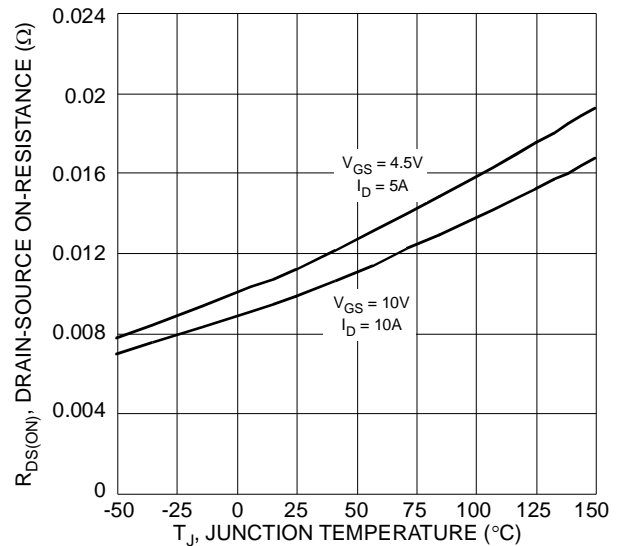
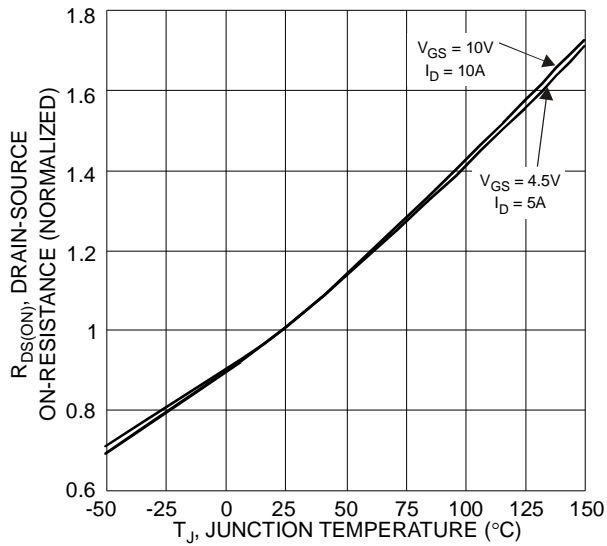
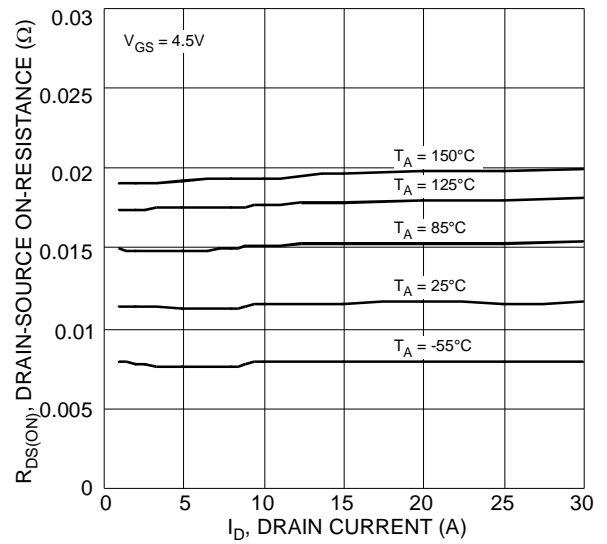
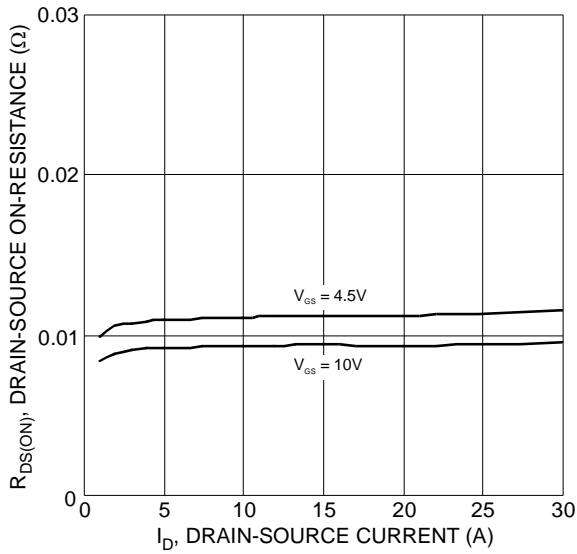


Figure 2 Typical Transfer Characteristics



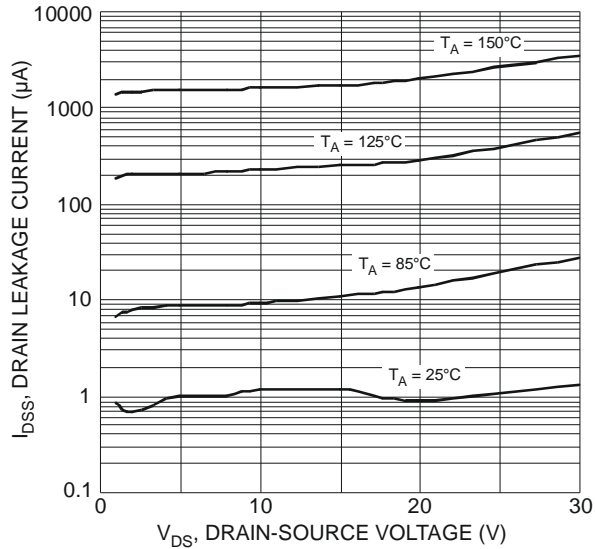


Figure 9 Typical Drain-Source Leakage Current vs. Voltage

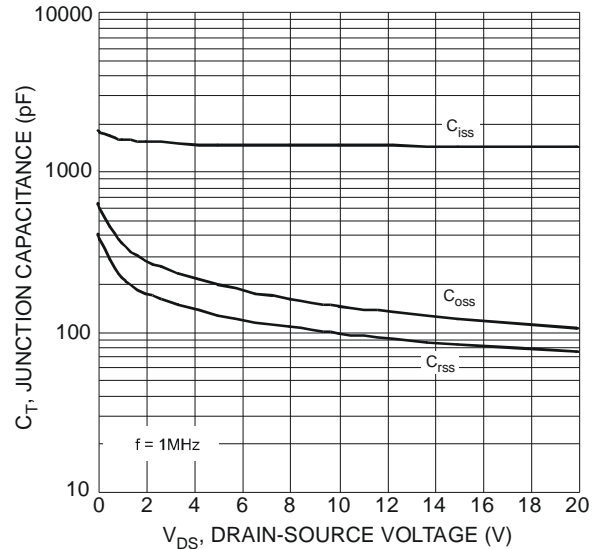


Figure 10 Typical Junction Capacitance

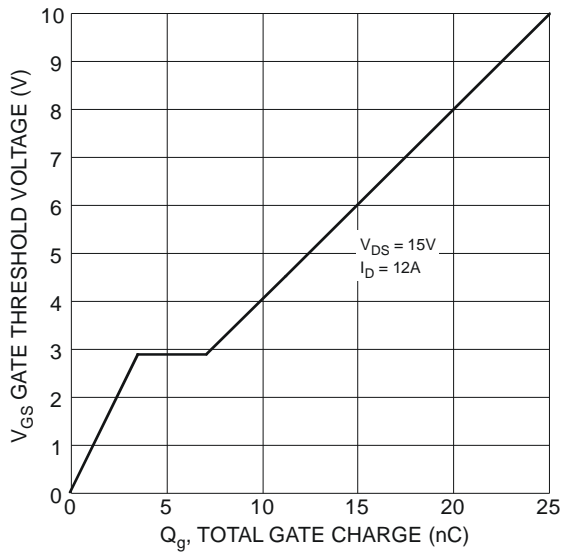


Figure 11 Gate Charge

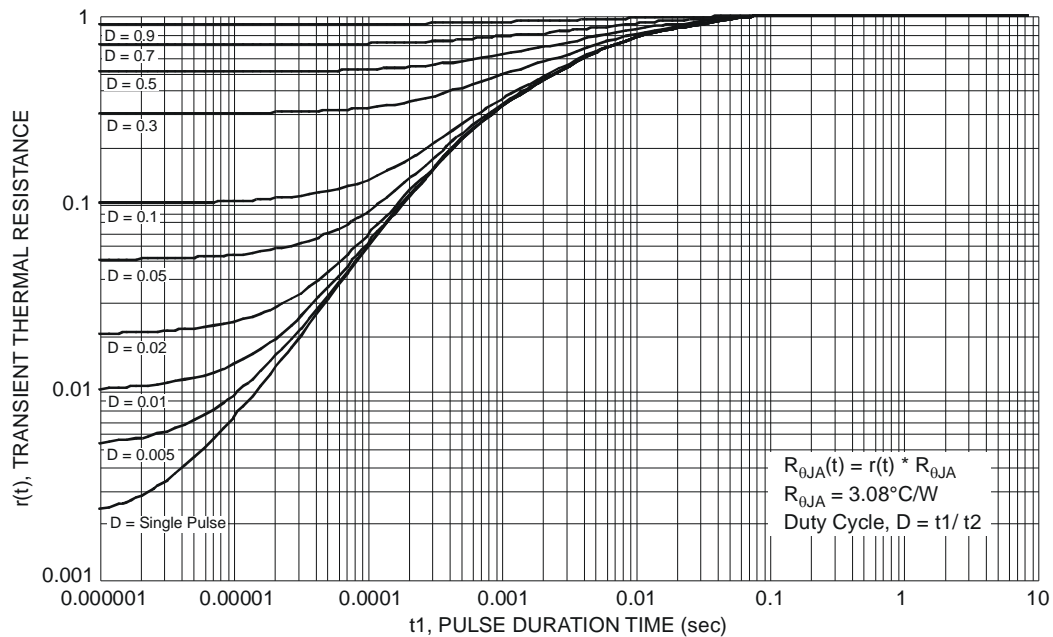
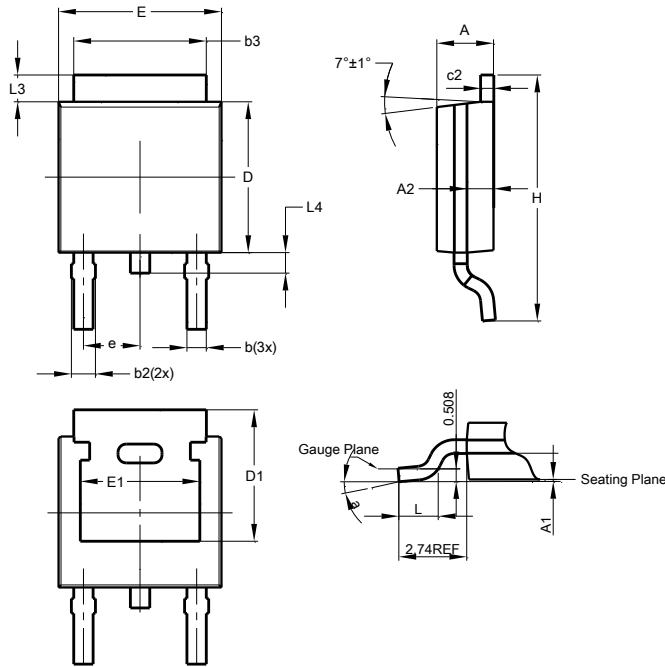


Figure 12 Transient Thermal Resistance

Package Outline Dimensions

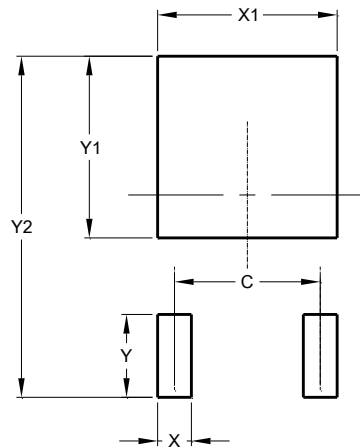
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.



TO252			
Dim	Min	Max	Typ
A	2.19	2.39	2.29
A1	0.00	0.13	0.08
A2	0.97	1.17	1.07
b	0.64	0.88	0.783
b2	0.76	1.14	0.95
b3	5.21	5.46	5.33
c2	0.45	0.58	0.531
D	6.00	6.20	6.10
D1	5.21	—	—
e	—	—	2.286
E	6.45	6.70	6.58
E1	4.32	—	—
H	9.40	10.41	9.91
L	1.40	1.78	1.59
L3	0.88	1.27	1.08
L4	0.64	1.02	0.83
a	0°	10°	—
All Dimensions in mm			

Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
C	4.572
X	1.060
X1	5.632
Y	2.600
Y1	5.700
Y2	10.700

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